



#15/C
Amend C
4 Robinson
5/9/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Shunpei YAMAZAKI et al.) Group Art Unit: 2811
Serial No. 09/535,015) Examiner: S. Crane
Filed: March 24, 2000)
For: METHOD OF MANUFACTURING)
A SEMICONDUCTOR DEVICE)

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with
The United States Postal Service with sufficient postage as First
Class Mail in an envelope addressed to: Commissioner for Patents,
Washington, D.C. 20231, on February 24, 2003.

Adele M. Stamper
Adele M. Stamper

AMENDMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated October 23, 2002, please amend the above-
identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Please replace the first and second paragraphs on page 6 with the following:

A first embodiment of the present invention is characterized in that it comprises
steps of forming an amorphous silicon film; holding a metal element which promotes
crystallization of silicon in contact on the surface of the amorphous silicon film; crystallizing
the amorphous silicon film by implementing a first heat treatment to obtain a crystal silicon
film; forming a thermal oxide film on the surface of the crystal silicon film by implementing a
second heat treatment in the temperature range of 500° C to 700° C within an atmosphere
containing oxygen, hydrogen and fluorine; and eliminating the thermal oxide film.

RECEIVED
MAR - 4 2003
TECHNOLOGY CENTER 2800